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## **RFMD Expands Industry-Leading Portfolio of GaN-Based CATV Components**

### **RFMD's Newest Hybrid Power Doubler Amplifier Module Delivers Unmatched Power Savings and Design Flexibility for CATV Network Designers**

NEW ORLEANS, Oct 19, 2010 (GlobeNewswire via COMTEX News Network) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, today announced availability of the RFPD2650, a new gallium nitride-based hybrid power doubler amplifier that delivers industry-best low distortion performance with the flexibility to optimize for supply current or energy consumption. The RFPD2650 hybrid power doubler amplifier module is specifically designed for CATV infrastructure applications including hybrid fiber coaxial (HFC) optical nodes.

Power doublers are used in HFC networks to extend the range of signal transmission from the head-end to the consumer. To minimize the cost of delivering the signal to the edge of their networks, multi system operators (MSOs) prefer to use as few amplifiers as possible. MSOs are also increasingly seeking to minimize the operational expenses associated with the HFC network, most notably power consumption and reliability. The RFPD2650 power doubler addresses both of these customer concerns, as does the entire line-up of RFMD's GaN-based amplifiers.

The RFPD2650 supplies a minimum gain of 21dB over the entire 45-1003MHz frequency range. It can deliver up to 20% power or energy savings with no performance penalty in HFC networks, or it can be configured to provide 3dB higher distortion level performance with the same power consumption. With this unique blend of performance attributes, the RFPD2650 enables MSO system designers to select either industry-leading or energy saving ("green") performance -- all while maintaining the ease of use infrastructure OEMs have come to expect from industry-standard SOT115J packaged amplifier modules.

The RFPD2650 leverages GaN HEMT and GaAs pHEMT technology to provide the industry's best distortion performance, enabling longer range transmission. Maximum current is 450mA, and current consumption can be reduced dramatically to less than 370mA for applications requiring reduced distortion performance. Programmed to match the distortion level of competitive devices, RFMD's RFPD2650 delivers two watts of power consumption savings.

The RFPD2650 is available now in sample or production quantities and is priced at \$26.50 in quantities of 5,000. Interested parties can click on <http://www.rfmd.com/CS/Documents/RFPD2650DS.pdf> for additional information about the RFPD2650.

#### About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance semiconductor components. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at [www.rfmd.com](http://www.rfmd.com).

The RF Micro Devices, Inc. logo is available at <http://www.globenewswire.com/newsroom/prs/?pkgid=6436>

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in operating results, risks associated with the impact of global macroeconomic and credit

conditions on our business and the business of our suppliers and customers, our reliance on a few large customers for a substantial portion of our revenue, the rate of growth and development of wireless markets, our ability to bring new products to market, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on gallium arsenide (GaAs) for the majority of our products, dependence on third parties, and substantial reliance on international sales and operations. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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